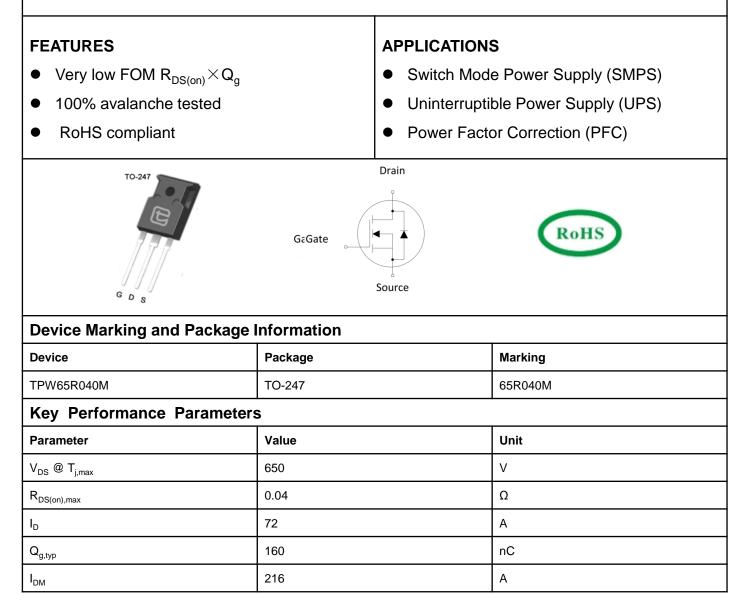


650V Super-Junction Power MOSFET

DESCRIPTION

650V super-junction Power MOSFET

Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The SJ MOSFET is a price-performance optimized product enabling to target cost sensitive applications in Consumer and Lighting markets, designed by Wuxi Unigroup Microelectronics Company.



Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted					
Parameter		Symbol	Value	Unit	
Drain-Source Voltage (V _{GS} = 0V)		V _{DSS}	650	V	
Continuous Drain Current	T _C = 25°C	l _D	72	А	
	TC = 100°C		43.2		
Pulsed Drain Current (note1)		I _{DM}	216	А	
Gate-Source Voltage		V _{GSS}	±30	V	
Single Pulse Avalanche Energy (note2)		E _{AS}	2185	mJ	
Repetitive Avalanche Energy (note2)		E _{AR}	3.31	mJ	
Avalanche Current		I _{AR}	13.7	A	
MOSFET dv/dt ruggedness, V _{DS} = 0480V		dv/dt	50	V/ns	
Power Dissipation		P _D	500	W	
Continuous Body Diode Current		۱ _s	61		
Pulsed Diode Forward Current (note1)		I _{SM}	216	A	
Reverse diode dv/dt (note3)		dv/dt	15	V/ns	
Maximum diode commutation speed (note3)		di _f /dt	500	A/us	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55~+150	°C	

Thermal Resistance				
Parameter	Symbol	Value	Unit	
Thermal Resistance, Junction-to-Case	R _{thJC}	0.25 °C/W		
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62	~C/W	



Devenueter			Value				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250\mu A$	650			V	
Zero Gate Voltage Drain Current		$V_{DS} = 650V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA	
	I _{DSS}	$V_{DS} = 650V, V_{GS} = 0V, T_{J} = 150^{\circ}C$			100		
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 30 V$			±100	nA	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5		4.5	V	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 25A		0.035	0.04	Ω	
Gate resistance	R _G	f = 1.0MHz open drain		0.3		Ω	
Dynamic							
Input Capacitance	C _{iss}			7565		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 100V,$		268			
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		3.3			
Total Gate Charge	Qg			160		nC	
Gate-Source Charge	Q _{gs}	$V_{DD} = 520V, I_{D} = 50A, V_{GS} = 10V$		38			
Gate-Drain Charge	Q _{gd}			60			
Turn-on Delay Time	t _{d(on)}			45			
Turn-on Rise Time	t _r	V _{DD} = 400V, I _D = 50A,		161			
Turn-off Delay Time	t _{d(off)}	$R_{\rm G} = 25\Omega$		287		ns	
Turn-off Fall Time	t _f			87			
Drain-Source Body Diode Characte	eristics			·			
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 72A, V _{GS} = 0V		0.9	1.2	V	
Reverse Recovery Time	t _{rr}			540		ns	
Reverse Recovery Charge	Q _{rr}	V _R = 400V, I _F = 30A, di _F /dt = 100A/µs		13.5		μC	
Peak Reverse Recovery Current	I _{rrm}			50.4		Α	

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. I_{AS} = 13.7A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 $^{\circ}$ C
- 3. Identical low side and high side switch with identical R_G



Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

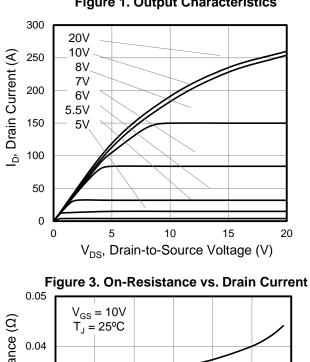
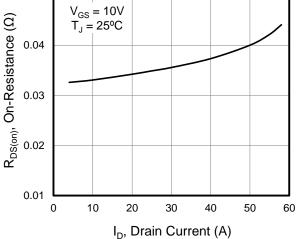
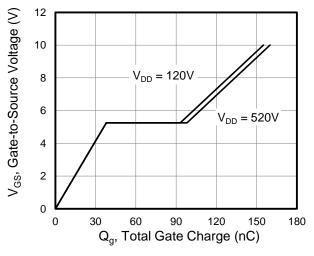


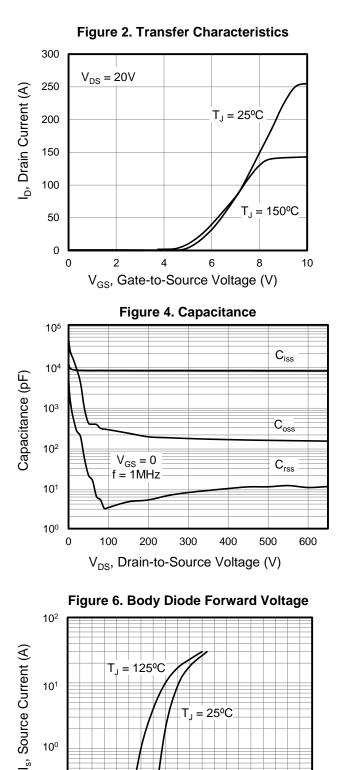
Figure 1. Output Characteristics











1.5

2

10⁰

10-1

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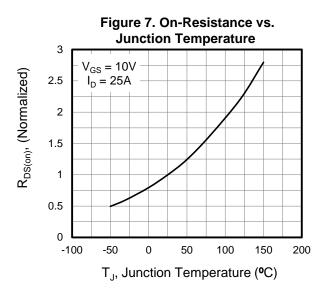
0.5

1

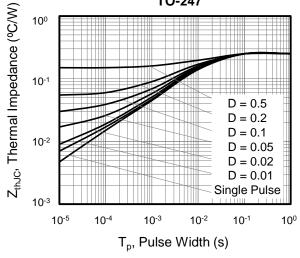
V_{SD}, Source-to-Drain Voltage (V)

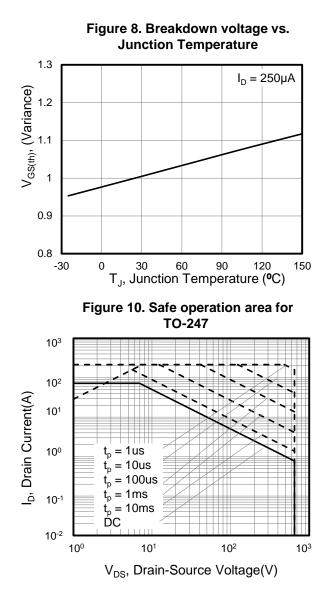


Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted











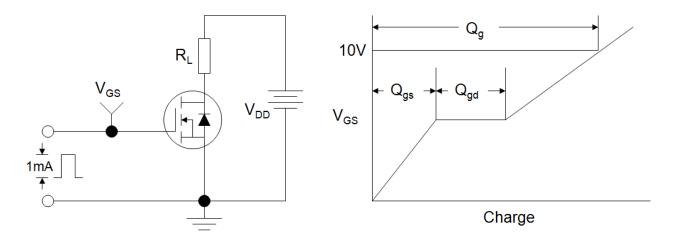


Figure B: Resistive Switching Test Circuit and Waveform

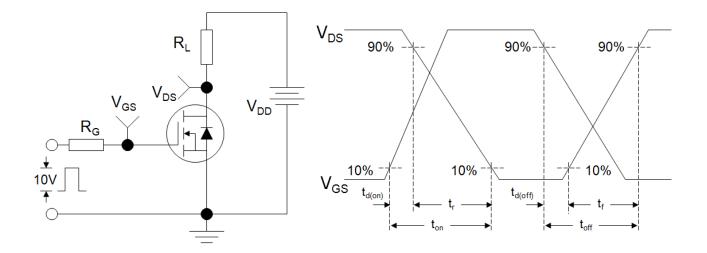
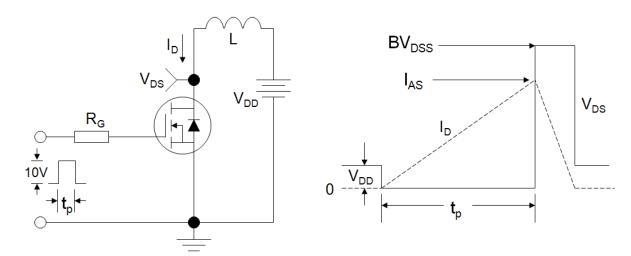
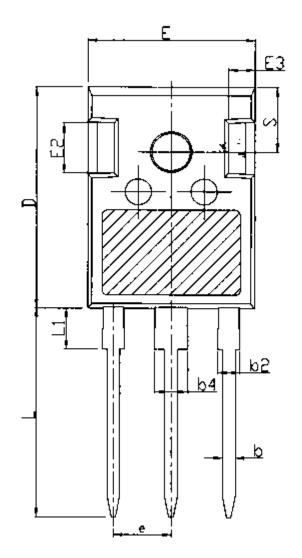


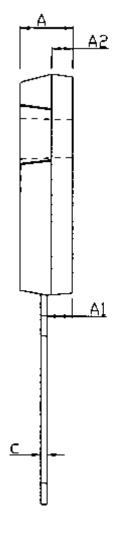
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

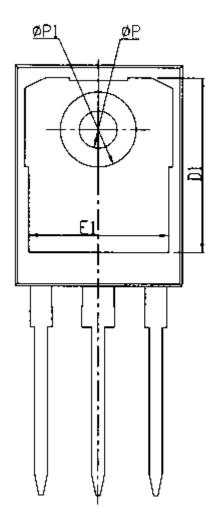


TO-247



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Unit:mm					
Symbol	Min.	Nom	Max.		
А	4.80	5.00	5.20		
A1	2.21	2.41	2.61		
A2	1.85	2.00	2.15		
b	1.11	1.21	1.36		
b2	1.91	2.01	2.21		
b4	2.91	3.01	3.21		
с	0.51	0.61	0.75		
D	20.70	21.00	21.30		
D1	16.25	16.55	16.85		

Unit:mm				
Symbol	Min. Nom. M		Max.	
E	15.50	15.80	16.10	
E1	13.00	13.30	13.60	
E2	4.80	5.00	5.20	
E3	2.30	2.50	2.70	
е	5.44BSC			
L	19.62	19.92	20.22	
L1	-	-	4.30	
ΦΡ	3.40	3.60	3.80	
ΦΡ1	-	-	7.30	
S	6.15BSC			



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